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# HM62832UH Series

256 k High Speed SRAM (32-kword × 8-bit)

# HITACHI

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## Features

- High speed: Fast access time 15/20 ns (max)
- Low Power  
Standby: 15  $\mu$ W (typ) (L-version)  
Operation: 675/600 mW (typ)
- Single 5 V supply
- Completely static memory  
No clock or timing strobe required
- Equal access and cycle times
- Common data input and output: Three state output
- Directly TTL compatible: All inputs and outputs

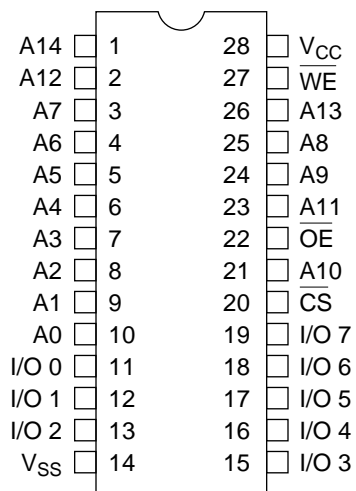
## Ordering Information

Type No.	Access Time	Package
HM62832UHP-15	15 ns	300-mil 28-pin plastic DIP (DP-28NA)
HM62832UHP-20	20 ns	
HM62832UHLP-15	15 ns	
HM62832UHLP-20	20 ns	
HM62832UHJP-15	15 ns	300-mil 28-pin plastic SOJ (CP-28DN)
HM62832UHJP-20	20 n	
HM62832UHLJP-15	15 ns	
HM62832UHLJP-20	20 ns	

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# HM62832UH Series

## Pin Arrangement

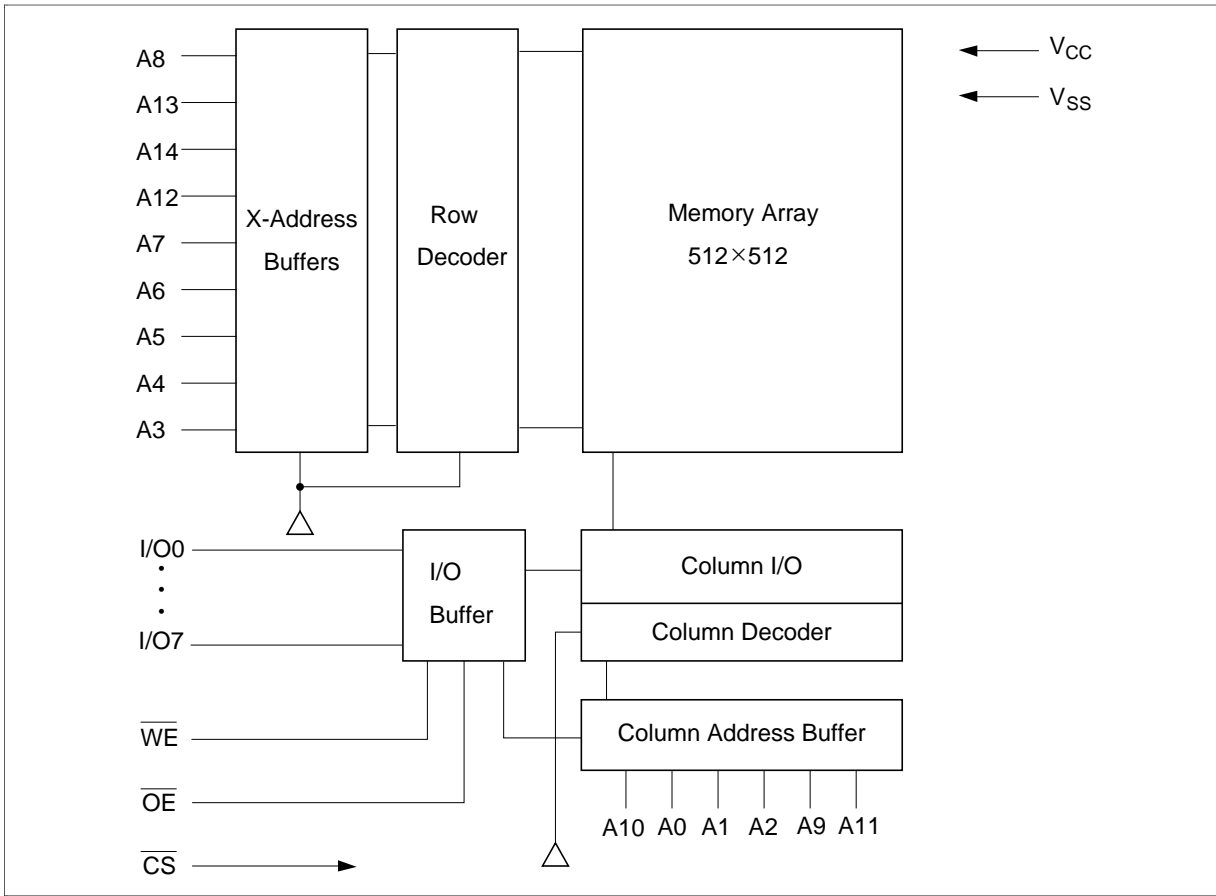


(Top view)

## Pin Description

Pin name	Function
A0 – A14	Address
I/O0 – I/O7	Input/output
CS	Chip select
WE	Write enable
OE	Output enable
V <sub>CC</sub>	Power supply
V <sub>SS</sub>	Ground

Block Diagram



Function Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	V <sub>CC</sub> Current	I/O Pin	Ref. Cycle
H	X	X	Standby	I <sub>SB</sub> , I <sub>SB1</sub>	High-Z	
L	L	H	Read	I <sub>CC</sub>	Dout	Read cycle 1, 2, 3
L	H	L	Write	I <sub>CC</sub>	Din	Write cycle 1
L	L	L	Write	I <sub>CC</sub>	Din	Write cycle 2

Note: X : H or L

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## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage <sup>1</sup>	$V_{CC}$	-0.5 <sup>2</sup> to +7.0	V
Voltage on any pin relative to $V_{SS}$ <sup>1</sup>	$V_T$	-0.5 <sup>2</sup> to $V_{CC} + 0.5$	V
Power dissipation	$P_T$	1.0	W
Operating temperature	$T_{opr}$	0 to +70	°C
Storage temperature	$T_{stg}$	-55 to +125	°C
Storage temperature under bias	$T_{bias}$	-10 to +85	°C

Notes: 1. With respect to  $V_{SS}$

2.  $V_{CC}$  and  $V_T$  min = -2.5 V for pulse width  $\leq 10$  ns

## Recommended DC Operating Conditions ( $T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	$V_{CC}$	4.5	5.0	5.5	V
	$V_{SS}$	0	0	0	V
Input high (logic 1) voltage	$V_{IH}$	2.2	—	$V_{CC} + 0.5$	V
Input low (logic 0) voltage	$V_{IL}$	-0.5 <sup>1</sup>	—	0.8	V

Note: 1.  $V_{IL}$  min = -2.0 V for pulse width  $\leq 10$  ns

**DC Characteristics** ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5\text{ V} \pm 10\%$ ,  $V_{SS} = 0\text{ V}$ )

Parameter	Symbol	Min	Typ <sup>*1</sup>	Max	Unit	Test Conditions
Input leakage current	$ I_{IL} $	—	—	2.0	$\mu\text{A}$	$V_{CC} = 5.5\text{ V}$ $V_{in} = V_{SS}$ to $V_{CC}$
Output leakage current	$ I_{LO} $	—	—	2.0	$\mu\text{A}$	$\overline{CS} = V_{IH}$ $V_{IO} = V_{SS}$ to $V_{CC}$
Operating $V_{CC}$ current	$I_{CC1} (-15)^{\text{*3}}$	—	135	170	mA	min cycle <sup>*2</sup>
	$I_{CC2} (-15)$	—	100	120	mA	2x min cycle
	$I_{CC1} (-20)$	—	120	150	mA	min cycle
	$I_{CC2} (-20)$	—	90	110	mA	2x min cycle
Standby $V_{CC}$ current	$I_{SB} (-15)$	—	40	60	mA	$\overline{CS} = V_{IH}$ , min cycle
	$I_{SB} (-20)$	—	30	50		
Standby $V_{CC}$ current (1)	$I_{SB1} (\text{L-version})$	—	0.02	2.0	mA	$\overline{CS} \geq V_{CC} - 0.2\text{ V}$ $0\text{ V} \leq V_{in} \leq 0.2\text{ V}$ or $V_{CC} - 0.2\text{ V} \leq V_{in}$
		—	0.003	0.1		
Output low voltage	$V_{OL}$	—	—	0.4	V	$I_{OL} = 8\text{ mA}$
Output high voltage	$V_{OH}$	2.4	—	—	V	$I_{OH} = -4.0\text{ mA}$

Notes: 1. Typical values are at  $V_{CC} = 5.0\text{ V}$ ,  $T_a = 25^\circ\text{C}$  and not guaranteed.

2.  $\overline{CS} = V_{IL}$ ,  $I_{out} = 0\text{ mA}$

3. Access time version

**Capacitance** ( $T_a = 25^\circ\text{C}$ ,  $f = 1.0\text{ MHz}$ )<sup>\*1</sup>

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance	$C_{in}$	—	—	6	pF	$V_{in} = 0\text{ V}$
Output capacitance	$C_{out}$	—	—	10	pF	$V_{IO} = 0\text{ V}$

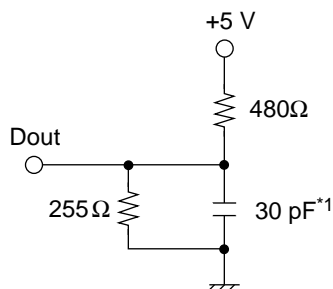
Note: 1. This parameter is sampled and not 100% tested.

# HM62832UH Series

**AC Characteristics** ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5\text{ V} \pm 10\%$ , unless otherwise noted.)

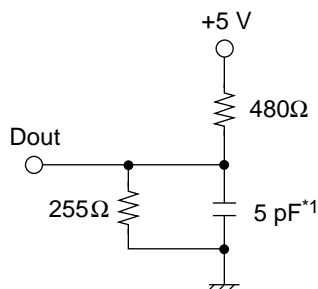
## Test Conditions

- Input pulse levels:  $V_{SS}$  to 3.0 V
- Input rise and fall time: 4 ns
- Input and Output timing reference levels: 1.5 V
- Output load: See figures



Output load (A)

Note: 1. Including scope and jig



Output load (B)

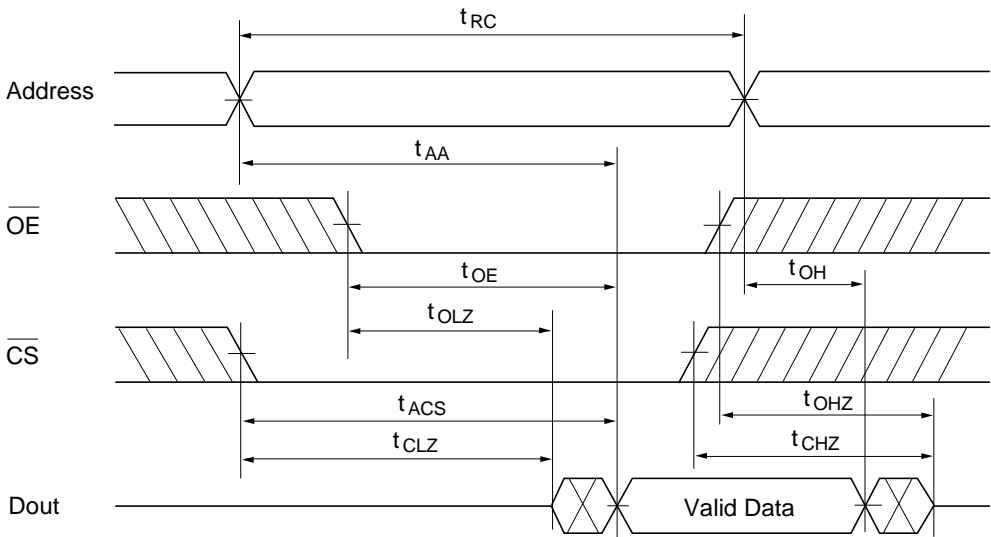
(for  $t_{CLZ}$ ,  $t_{OLZ}$ ,  $t_{CHZ}$ ,  $t_{OHZ}$ ,  $t_{WHZ}$  and  $t_{OW}$ )

## Read Cycle

Parameter	Symbol	HM62832UH-15		HM62832UH-20		Unit
		Min	Max	Min	Max	
Read cycle time	$t_{RC}$	15	—	20	—	ns
Address access time	$t_{AA}$	—	15	—	20	ns
Chip select access time	$t_{ACS}$	—	15	—	20	ns
Chip selection to output in low-Z	$t_{CLZ}^{*1}$	3	—	3	—	ns
Output enable to output valid	$t_{OE}$	—	8	—	10	ns
Output enable to output in low-Z	$t_{OLZ}^{*1}$	0	—	0	—	ns
Chip deselection to output in high-Z	$t_{CHZ}^{*1}$	0	7	0	10	ns
Chip disable to output in high-Z	$t_{OHZ}^{*1}$	0	7	0	10	ns
Output hold from address change	$t_{OH}$	3	—	3	—	ns

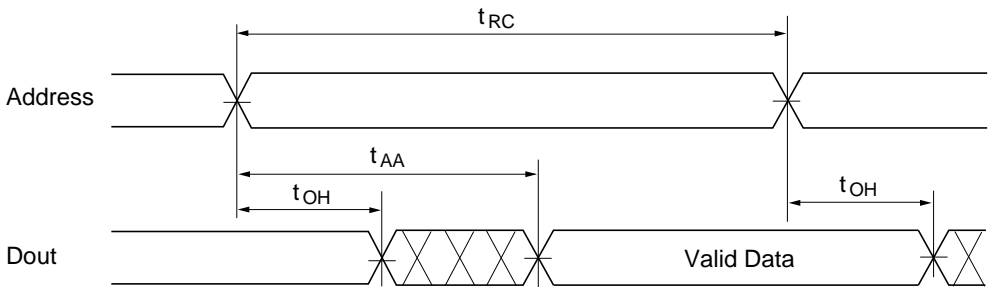
Note: 1. Transition is measured  $\pm 200$  mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

Read Timing Waveform (1)<sup>\*1</sup> ( $\overline{WE} = V_{IH}$ )



Note: 1. Transition is measured  $\pm 200$  mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

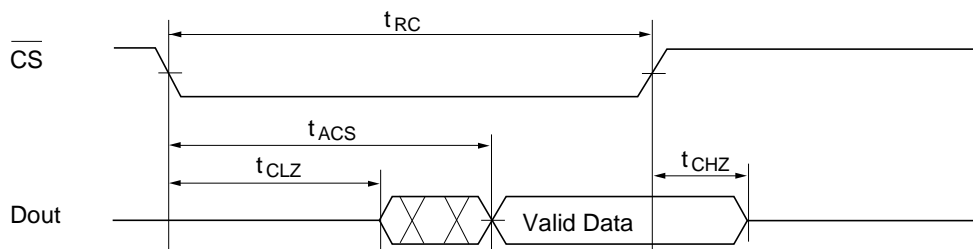
Read Timing Waveform (2)<sup>\*1</sup> ( $\overline{WE} = V_{IH}, \overline{CS} = V_{IL}, \overline{OE} = V_{IL}$ )



Note: 1. Transition is measured  $\pm 200$  mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

# HM62832UH Series

## Read Timing Waveform (3) <sup>\*1, \*2</sup> ( $\overline{WE} = V_{IH}, \overline{OE} = V_{IL}$ )



- Notes: 1. Transition is measured  $\pm 200$  mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.  
 2. Address valid prior to or coincident with  $\overline{CS}$  transition low.

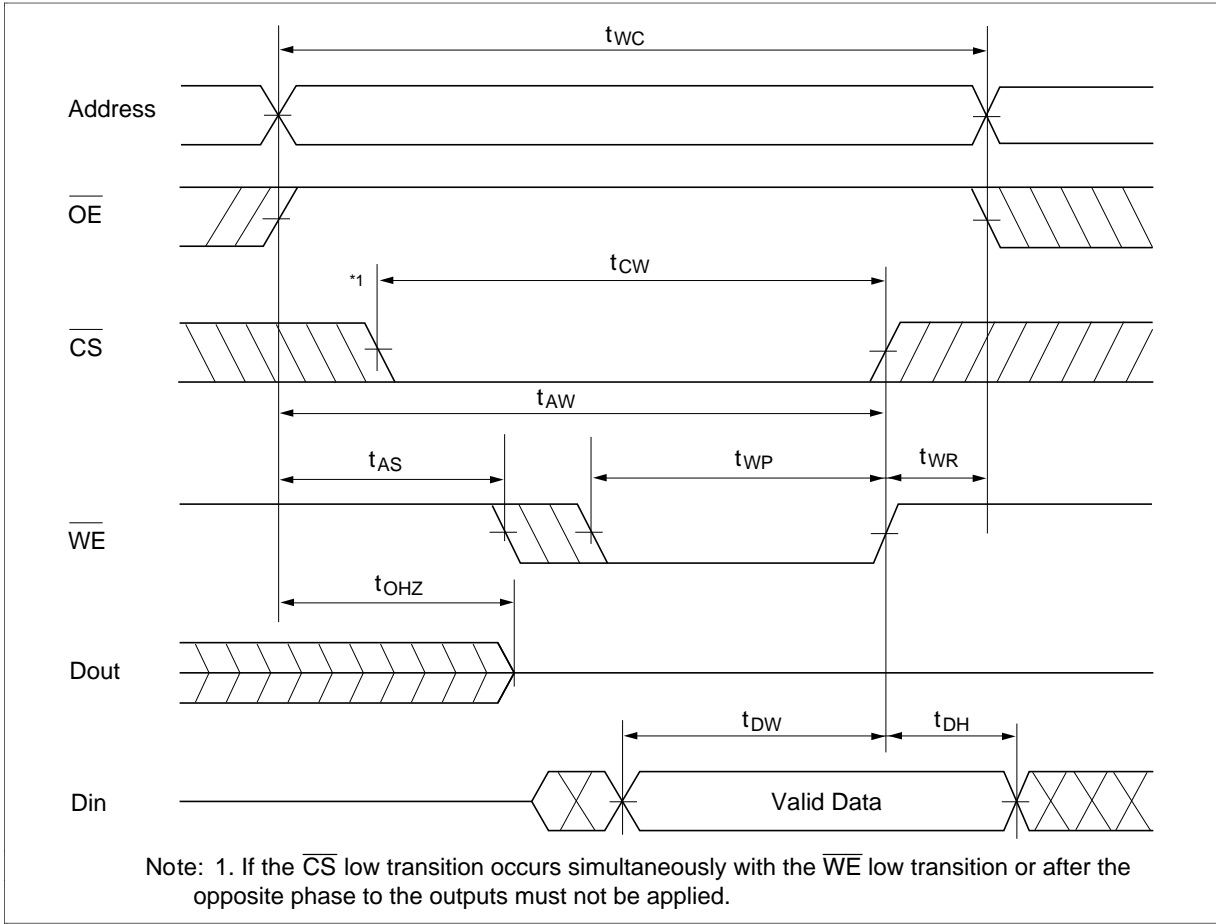
## Write Cycle

Parameter	Symbol	HM62832UH-15		HM62832UH-20		Unit
		Min	Max	Min	Max	
Write cycle time	$t_{WC}$	15	—	20	—	ns
Chip selection to end of write	$t_{CW}$	10	—	12	—	ns
Address valid to end of write	$t_{AW}$	13	—	15	—	ns
Address setup time	$t_{AS}$	0	—	0	—	ns
Write pulse width <sup>*2</sup>	$t_{WP}$	10	—	12	—	ns
Write recovery time <sup>*3</sup>	$t_{WR}$	0	—	0	—	ns
Output disable to output in high-Z <sup>*1, 4</sup>	$t_{OHZ}$	0	7	0	10	ns
Write to output in high-Z <sup>*1, 4</sup>	$t_{WHZ}$	0	7	0	10	ns
Data to write time overlap	$t_{DW}$	8	—	10	—	ns
Data hold from write time <sup>*6</sup>	$t_{DH}$	0	—	0	—	ns
Output active from end of write <sup>*1, 6</sup>	$t_{OW}$	3	—	3	—	ns
Output hold from address change <sup>*5</sup>	$t_{OH}$	3	—	3	—	ns

- Notes: 1. Transition is measured  $\pm 200$  mV from high impedance voltage with Load (B). This parameter is sampled and not 100% tested.  
 2. A write occurs during the overlap ( $t_{WP}$ ) to a low  $\overline{CS}$  and a low  $\overline{WE}$ .  
 3.  $t_{WR}$  is measured from the earliest of  $\overline{CS}$  or  $\overline{WE}$  going high to the end of write cycle.  
 4. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.  
 5.  $Dout$  is the same phase of write data of this write cycle.  
 6. If  $\overline{CS}$  is low during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.

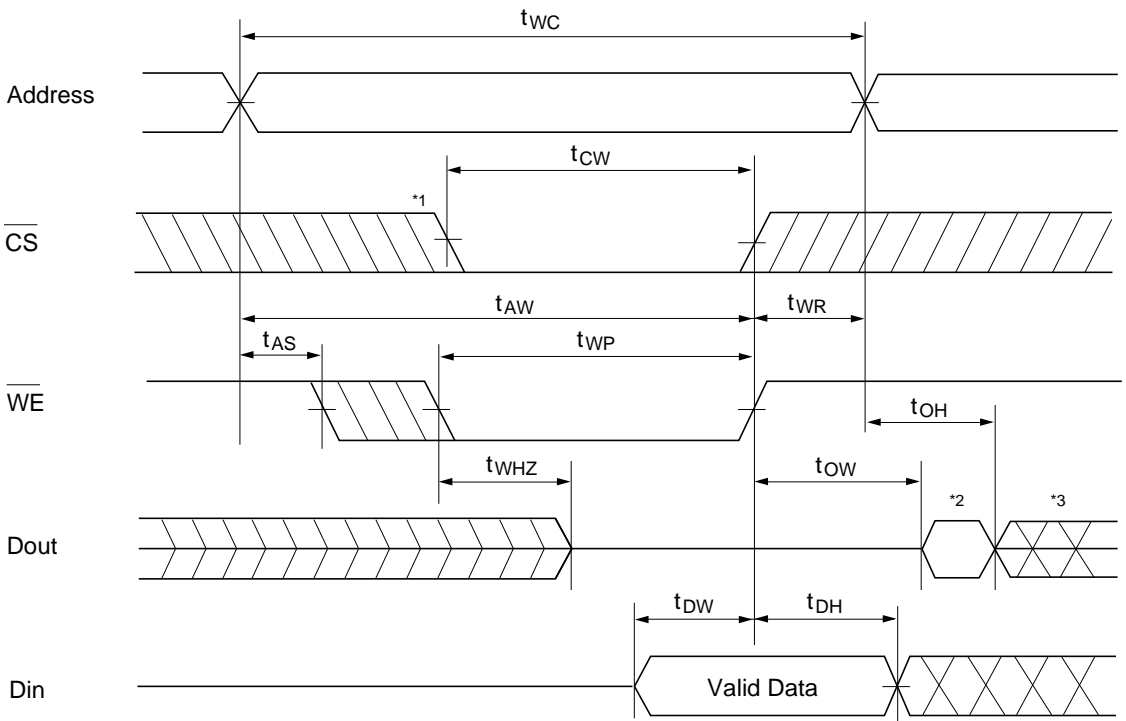


Write Timing Waveform (1)



# HM62832UH Series

## Write Timing Waveform (2) ( $\overline{\text{OE}}$ low Fixed)<sup>\*4</sup>



- Notes:
1. If the  $\overline{\text{CS}}$  low transition occurs simultaneously with the  $\overline{\text{WE}}$  low transitions or after the  $\overline{\text{WE}}$  transition, output remain in a high impedance state.
  2. Dout is the same phase of write data of this write cycle.
  3. Dout is the read data of next address.
  4.  $\overline{\text{WE}}$  must be high during all address transition except when device is disable with  $\overline{\text{CS}}$ .

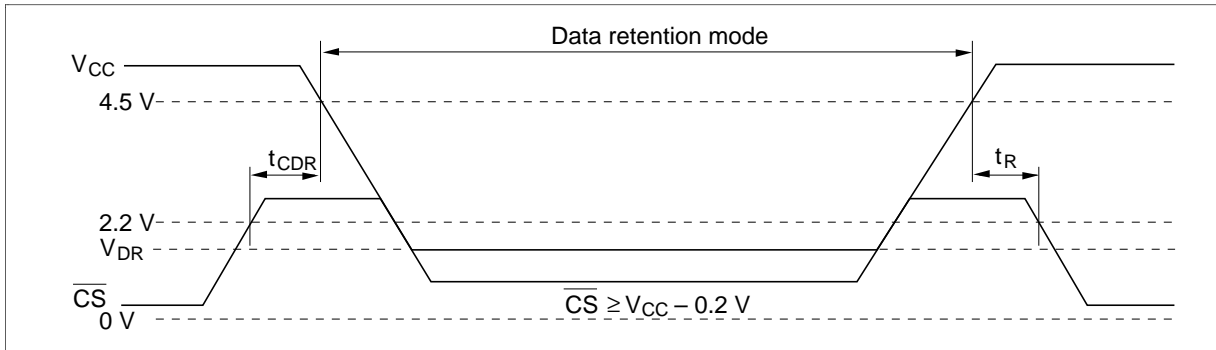
**Low  $V_{CC}$  Data Retention Characteristics ( $T_a = 0$  to  $+70^\circ\text{C}$ )**

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
$V_{CC}$ for data retention	$V_{DR}$	2	—	—	V	$\overline{CS} \geq V_{CC} - 0.2\text{V}$ , $V_{in} \geq V_{CC} - 0.2\text{V}$ or $0\text{V} < V_{in} \leq 0.2\text{V}$
Data retention current	$I_{CCDR}$	—	2	$50^{*1}$	$\mu\text{A}$	
Chip deselect to data retention time	$t_{CDR}$	0	—	—	ns	
Operation recovery time	$t_R$	5	—	—	ms	

Note: 1.  $V_{CC} = 3.0\text{V}$

**Low  $V_{CC}$  Data Retention Timing Waveform**

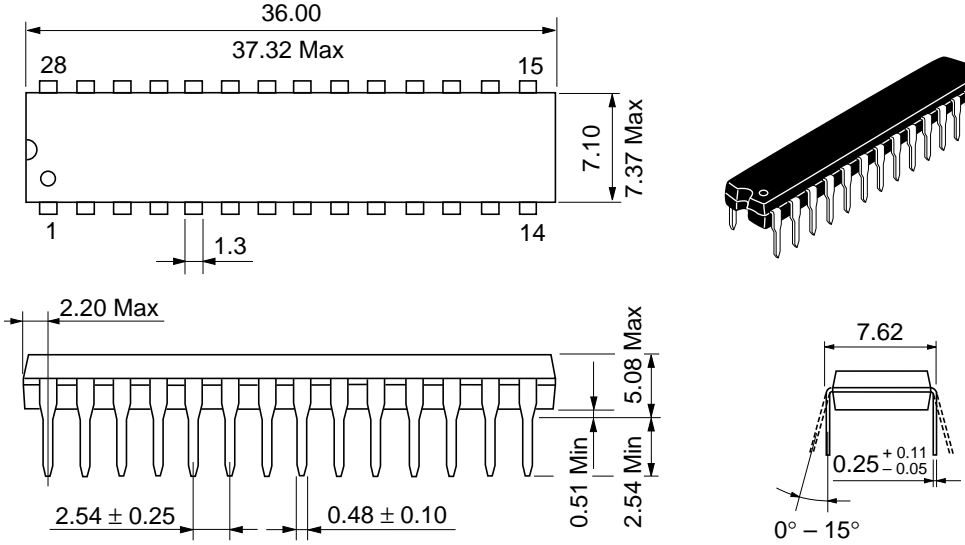


# HM62832UH Series

## Package Dimensions

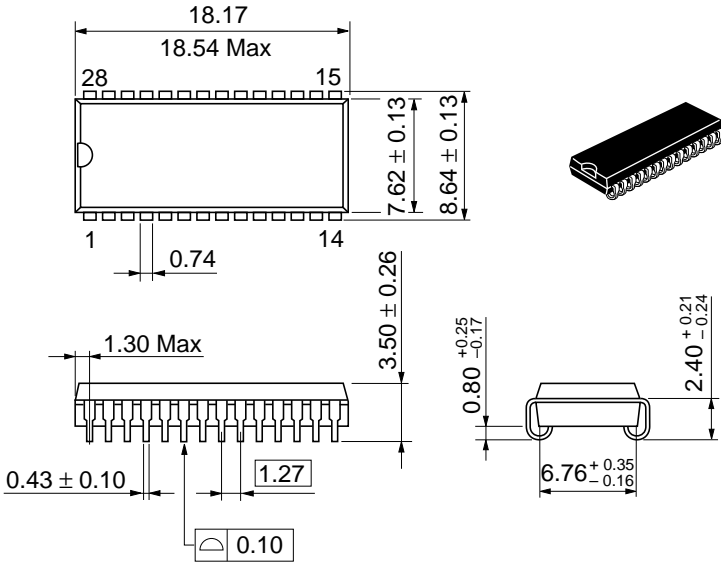
HM62832UHP/UHLP Series (DP-28NA)

Unit: mm



HM62832UHJP/UHLJP Series (CP-28DN)

Unit: mm



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